

RoHS

HALOGEN

**FRFF** 

# Improved Quad SPST CMOS Analog Switches

### **DESCRIPTION**

The DG441B, DG442B are monolithic quad analog switches designed to provide high speed, low error switching of analog and audio signals. The DG441B, DG442B are upgrades to the original DG441, DG442.

Combing low on-resistance (45  $\Omega$ , typ.) with high speed  $(t_{ON}\,120\,$  ns, typ.), the DG441B, DG442B are ideally suited for Data Acquisition, Communication Systems, Automatic Test Equipment, or Medical Instrumentation. Charge injection has been minimized on the drain for use in sample-and-hold circuits.

The DG441B, DG442B are built using Vishay Siliconix's high-voltage silicon-gate process. An epitaxial layer prevents latchup.

When on, each switch conducts equally well in both directions and blocks input voltages to the supply levels when off.

### **FEATURES**

- Halogen-free according to IEC 61249-2-21 Definition
- Low On-Resistance: 45  $\Omega$
- Low Power Consumption: 1 mW
- Fast Switching Action t<sub>ON</sub>: 120 ns
- Low Charge Injection Q: 1 pC
- TTL/CMOS-Compatible Logic
- Single Supply Capability
- Compliant to RoHS Directive 2002/95/EC

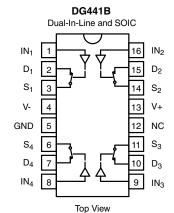
### **BENEFITS**

- Less Signal Errors and Distortion
- Reduced Power Supply Requirements
- Faster Throughput
- Reduced Pedestal Errors
- Simple Interfacing

### **APPLICATIONS**

- Audio Switching
- **Data Acquisition**
- Sample-and-Hold Circuits
- Communication Systems
- Automatic Test Equipment
- Medical Instruments

### FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



DC441B

	DG441B QFN16 (4 x 4 mm)					
	$D_1$ $IN_1$ $IN_2$ $D_2$					
S <sub>1</sub> V-	16 15 14 13	S <sub>2</sub> V+				
GND	3 10	NC				
S <sub>4</sub>	4 5 6 7 8	S <sub>3</sub>				
	D <sub>4</sub> IN <sub>4</sub> IN <sub>3</sub> D <sub>3</sub>					
	Top View					

TRUTH TABLE							
Logic	DG441B	DG442B					
0	ON	OFF					
1	OFF	ON					

Logic "0" ≤ 0.8 V Logic "1" ≥ 2.4 V

ORDERING INFORMATION							
Temp Range	Package	Part Number					
		DG441BDJ					
	16-pin Plastic DIP  DG441BDJ- DG442BDJ	DG441BDJ-E3					
		DG442BDJ					
		DG442BDJ-E3					
- 40 °C to 85 °C		DG441BDY-E3					
- 40 0 10 05 0	16-pin Narrow SOIC	DG441BDY-T1-E3					
	10-piii Naiiow 3010	DG442BDY-E3					
		DG442BDY-T1-E3					
	16 pin QFN 4 x 4 mm	DG441BDN-T1-E4					
	10 piii Qi N 4 X 4 IIIIII	DG442BDN-T1-E4					

Document Number: 72625 S11-1350-Rev. B, 04-Jul-11

# DG441B, DG442B

# Vishay Siliconix



<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)							
Parameter		Symbol	Limit	Unit			
V+ to V-			44				
GND to V-			25	V			
Digital Inputs <sup>a</sup> , V <sub>S</sub> , V <sub>D</sub>			(V-) - 2 to (V+) + 2 or 30 mA, whichever occurs first				
Continuous Current (Any Termina	al)		30	mA			
Current, S or D (Pulsed at 1 ms,	10 % duty cycle )		100				
Storage Temperature			- 65 to 125	°C			
	16-pin Plastic DIP <sup>c</sup>		470				
Power Dissipation (Package) <sup>b</sup>	16-pin Narrow Body SOIC <sup>d</sup>		900	mW			
	QFN-16 <sup>d</sup>		850				

a. Signals on  $S_X$ ,  $D_X$ , or  $IN_X$  exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC Board.

c. Derate 6 mW/°C above 75 °C.

d. Derate 12 mW/°C above 75 °C.



		Test Conditions		Limits			
		Unless Otherwise Specified V+ = 15 V. V- = - 15 V		- 4	0 °C to 85	°C	
Parameter	Symbol	$V_{+} = 15 \text{ V}, V_{-} = -15 \text{ V}$ $V_{L} = 5 \text{ V}, V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{e}$	Temp.b	Min. <sup>d</sup>	Typ. <sup>c</sup>	Max. <sup>d</sup>	Unit
Analog Switch		2 / 114 /	10		.,,,,	muxi	1 0
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	- 15		15	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full		45	80 95	
On-Resistance Match Between Channels <sup>e</sup>	ΔR <sub>DS(on)</sub>	$I_S = 1 \text{ mA}, V_D = \pm 10 \text{ V}$	Room Full		2	4 5	Ω
Switch Off Leakage Current	I <sub>S(off)</sub>	$V_D = \pm 14 \text{ V}, V_S = \pm 14 \text{ V}$	Room Full	- 0.5 - 5	± 0.01	0.5 5	
	I <sub>D(off)</sub>		Room Full	- 0.5 - 5	± 0.01	0.5 5	nA
Channel On Leakage Current	I <sub>D(on)</sub>	$V_S = V_D = \pm 14 \text{ V}$	Room Full	- 0.5 - 10	± 0.02	0.5 10	
Digital Control							
Input Voltage Low	V <sub>INL</sub>		Full			0.8	.,
Input Voltage High	V <sub>INH</sub>		Full	2.4			V
Input Current V <sub>IN</sub> Low	I <sub>INL</sub>	V <sub>IN</sub> under test = 0.8 V All Other = 2.4 V	Full	- 1	- 0.01	1	μΑ
Input Current V <sub>IN</sub> High	I <sub>INH</sub>	V <sub>IN</sub> under test = 2.4 V All Other = 0.8 V	Full	- 1	0.01	1	μΑ
Dynamic Characteristics							
Turn-On Time	t <sub>ON</sub>	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}$	Room		120	220	ns
Turn-Off Time	t <sub>OFF</sub>	V <sub>S</sub> = 10 V, See Figure 2	Room		65	120	113
Charge Injection <sup>e</sup>	Q	$C_L = 1 \text{ nF, } V_S = 0 \text{ V}$ $V_{gen} = 0 \text{ V, } R_{gen} = 0 \Omega$	Room		- 1		рС
Off Isolation <sup>e</sup>	OIRR	$R_L = 50 \Omega$ , $C_L = 15 pF$	Room	_	- 90		dB
Crosstalk (Channel-to-Channel)	X <sub>TALK</sub>	$V_S = 1 V_{RMS}$ , $f = 100 \text{ kHz}$	Room		- 95		ub
SourceOff Capacitance <sup>e</sup>	C <sub>S(off)</sub>	f = 1 MHz	Room		4		
Drain Off Capacitance <sup>e</sup>	C <sub>D(off)</sub>		Room		4		pF
Channel On Capacitance <sup>e</sup>	C <sub>D(on)</sub>	$V_S = V_D = 0 V$ , $f = 1 MHz$	Room		16		
Power Supplies						-	
Positive Supply Current	l+	V+ = 16.5 V, V- = - 16.5 V	Room Full			1 5	μА
Negative Supply Current	I-	V <sub>IN</sub> = 0 or 5 V	Room Full	- 1 - 5			μΑ
					•		



SPECIFICATIONS (for single supply)							
		Test Conditions Unless Otherwise Specified V+ = 12 V, V- = 0 V		- 4	Limits 0 °C to 85	°C	
Parameter	Symbol	$V_{IN} = 2.4 \text{ V}, 0.8 \text{ V}^{e}$	Temp.b	Min. <sup>d</sup>	Typ. <sup>c</sup>	Max. <sup>d</sup>	Unit
Analog Switch							
Analog Signal Range <sup>e</sup>	V <sub>ANALOG</sub>		Full	0		12	V
Drain-Source On-Resistance	R <sub>DS(on)</sub>	I <sub>S</sub> = 1 mA, V <sub>D</sub> = 3 V, 8 V	Room Full		90	160 200	Ω
Dynamic Characteristics			•				
Turn-On Time	t <sub>ON</sub>	$R_L = 1 \text{ k}\Omega, C_L = 35 \text{ pF}, V_S = 8 \text{ V}$	Room		120	300	ns
Turn-Off Time	t <sub>OFF</sub>	See Figure 2	Room		60	200	115
Charge Injection	Q	$C_L = 1 \text{ nF, } V_{gen} = 6 \text{ V, } R_{gen} = 0 \Omega$	Room		4		рC
Power Supplies							
Positive Supply Current	l+	V <sub>IN</sub> = 0 V or 5 V	Room Full			1 5	μΑ
Negative Supply Current	l-	V <sub>IN</sub> = 0 V OI 0 V	Room Full	- 1 - 5			μΑ

### Notes:

- a. Refer to PROCESS OPTION FLOWCHART.
- b. Room = 25  $^{\circ}$ C, Full = as determined by the operating temperature suffix.
- c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- e. Guaranteed by design, not subject to production test.
- f.  $V_{IN}$  = input voltage to perform proper function.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **SCHEMATIC DIAGRAM** (typical channel)

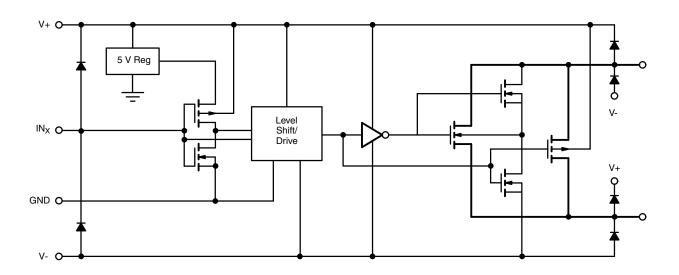
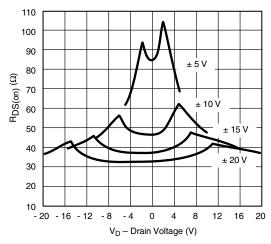


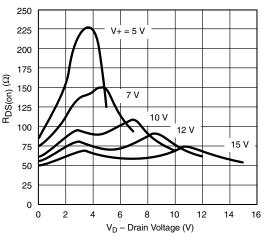
Figure 1.



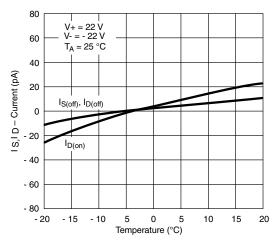
## **TYPICAL CHARACTERISTICS** $(T_A = 25 \, ^{\circ}\text{C}, \text{ unless otherwise noted})$



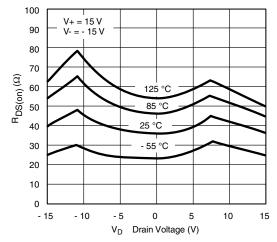
 $R_{DS(on)}$  vs.  $V_D$  and Power Supply Voltages



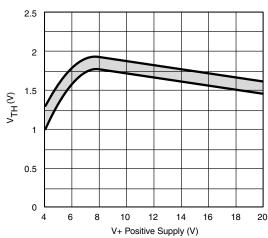
R<sub>DS(on)</sub> vs. V<sub>D</sub> and Single Power Supply Voltages



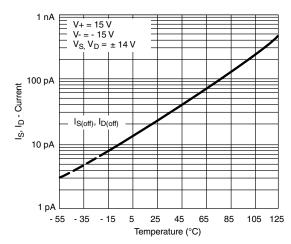
Leakage Currents vs. Analog Voltage



 $R_{DS(on)}$  vs.  $V_D$  and Temperature



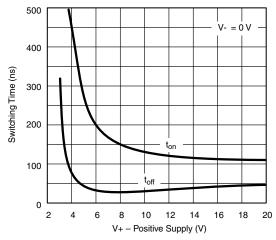
Input Switching Threshold vs. Supply Voltage



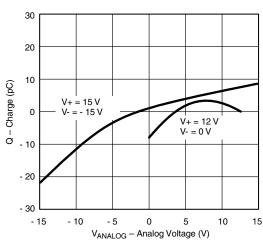
Leakage Currents vs. Temperature

# VISHAY

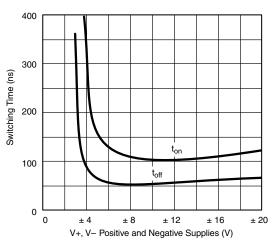
# **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)



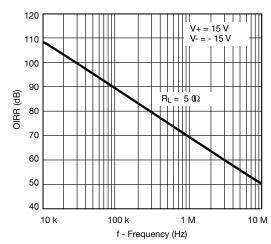
Switching Time vs. Single Supply Voltage



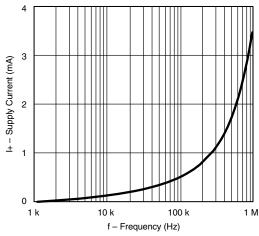
Q<sub>S</sub>, Q<sub>D</sub> - Charge Injection vs. Analog Voltage



**Switching Times vs. Power Supply Voltage** 



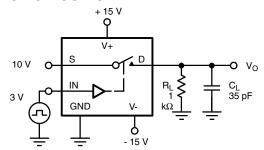
Off Isolation vs. Frequency



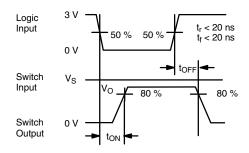
**Supply Current vs. Switching Frequency** 



## **TEST CIRCUITS**

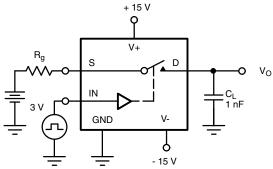


C<sub>L</sub> (includes fixture and stray capacitance)



Note: Logic input waveform is inverted for DG442.

Figure 2. Switching Time



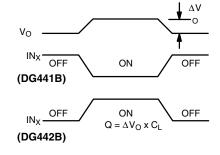
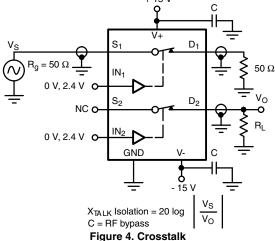


Figure 3. Charge Injection

C = 1 mF tantalum in parallel with 0.01 mF ceramic



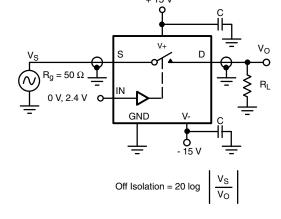


Figure 5. Off Isolation

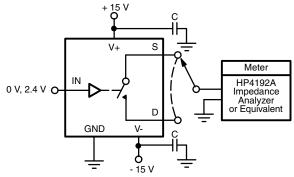
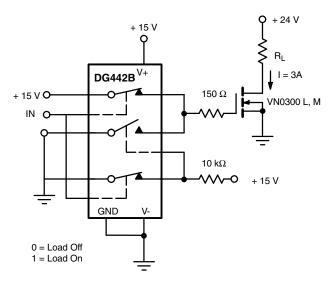


Figure 6. Source/Drain Capacitances

## **APPLICATIONS**





+ 15 V  $V_{IN}$ 1/4 DG442B D  $V_{\text{OUT}}$ IN O - 15 V H = Sample L = Hold

Figure 7. Power MOSFET Driver

Figure 8. Open Loop Sample-and-Hold

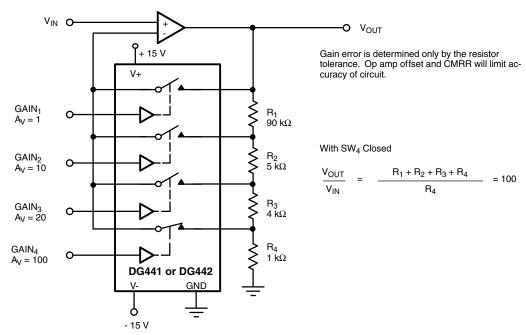


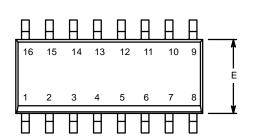
Figure 9. Precision-Weighted Resistor Programmable-Gain Amplifier

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72625.





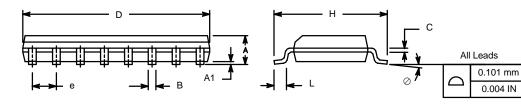
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIMETERS		INC	HES			
Dim	Min	Max	Min	Max			
Α	1.35	1.75	0.053	0.069			
A <sub>1</sub>	0.10	0.20	0.004	0.008			
В	0.38	0.51	0.015	0.020			
С	0.18	0.23	0.007	0.009			
D	9.80	10.00	0.385	0.393			
E	3.80	4.00	0.149	0.157			
е	1.27	BSC	0.050	BSC			
Н	5.80	6.20	0.228	0.244			
L	0.50	0.93	0.020	0.037			
0	0°	8°	0°	8°			
FCN: S-03946—Rev. F. 09-Jul-01							

ECN: S-03946—Rev. F, 09-Jul-01

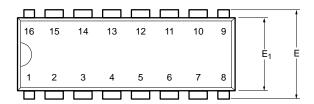
DWG: 5300

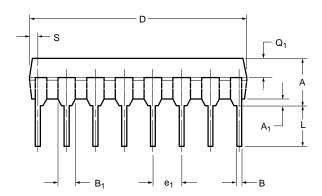


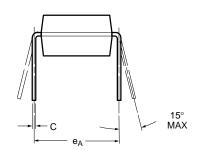
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



PDIP: 16-LEAD







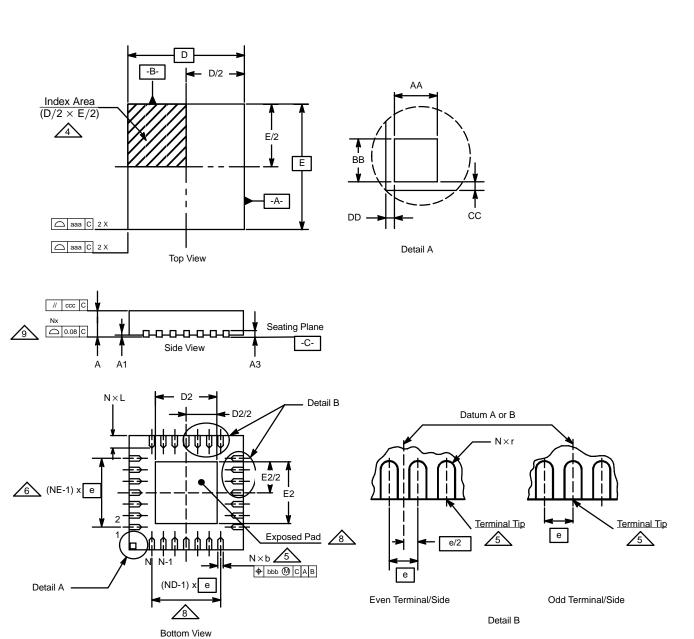
	MILLIN	IETERS	INC	HES			
Dim	Min	Max	Min	Max			
Α	3.81	5.08	0.150	0.200			
A <sub>1</sub>	0.38	1.27	0.015	0.050			
В	0.38	0.51	0.015	0.020			
B <sub>1</sub>	0.89	1.65	0.035	0.065			
С	0.20	0.30	0.008	0.012			
D	18.93	21.33	0.745	0.840			
E	7.62	8.26	0.300	0.325			
E <sub>1</sub>	5.59	7.11	0.220	0.280			
e <sub>1</sub>	2.29	2.79	0.090	0.110			
e <sub>A</sub>	7.37	7.87	0.290	0.310			
L	2.79	3.81	0.110	0.150			
Q <sub>1</sub>	1.27	2.03	0.050	0.080			
S	0.38	1.52	.015	0.060			
	ECN: S-03946—Rev. D, 09-Jul-01 DWG: 5482						

Document Number: 71261 www.vishay.com 06-Jul-01 www.vishay.com



## QFN-16 (4×4 mm)

JEDEC Part Number: MO-220



Document Number: 71921 www.vishay.com 19-Aug-02

# **Package Information**

# **Vishay Siliconix**

QFN-16 (4×4 mm)

JEDEC Part Number: MO-220



	MII	<b>MILLIMETERS*</b>			INCHES			ERS* INCHES		
Dim	Min	Nom	Max	Min	Nom	Max	Notes			
Α	0.80	0.90	1.00	0.0315	0.0354	0.0394				
A1	0	0.02	0.05	0	0.0008	0.0020				
A3	-	0.20 Ref	-	-	0.0079	-				
AA	-	0.345	-	-	0.0136	-				
aaa	-	0.25	-	-	0.0098	-				
BB	-	0.345	=	-	0.0136	-				
b	0.23	0.30	0.38	0.0091	0.0118	0.0150	5			
bbb	-	0.10	-	-	0.0039	-				
CC	-	0.18	-	-	0.0071	-				
CCC	-	0.10	-	-	0.0039	-				
D		4.00 BSC			0.1575 BSC					
D2	2.00	2.15	2.25	0.0787	0.0846	0.0886				
DD	-	0.18	-	-	0.0071	-				
Е		4.00 BSC			0.1575 BSC					
E2	2.00	2.15	2.25	0.0787	0.0846	0.0886				
е		0.65 BSC			0.0256 BSC					
L	0.45	0.55	0.65	0.0177	0.0217	0.0256				
N		16			16		3, 7			
ND	-	4	=	-	4	-	6			
NE	-	4	=	-	4	-	6			
r	b(min)/2	-	-	b(min)/2	-	-				

<sup>\*</sup> Use millimeters as the primary measurement.

ECN: S-21437—Rev. A, 19-Aug-02 DWG: 5890

### NOTES:

- Dimensioning and tolerancing conform to ASME Y14.5M-1994.
- All dimensions are in millimeters. All angels are in degrees.
- 3. N is the total number of terminals.

The terminal #1 identifier and terminal numbering convention shall conform to JESD 95-1 SPP-012. Details of terminal #1 identifier are optional, but must be located within the zone indicated. The terminal #1 identifier may be either a molded or marked feature. The X and Y dimension will vary according to lead counts.

5. Dimension b applies to metallized terminal and is measured between 0.25 mm and 0.30 mm from the terminal tip.

6 ND and NE refer to the number of terminals on the D and E side respectively.

Depopulation is possible in a symmetrical fashion.

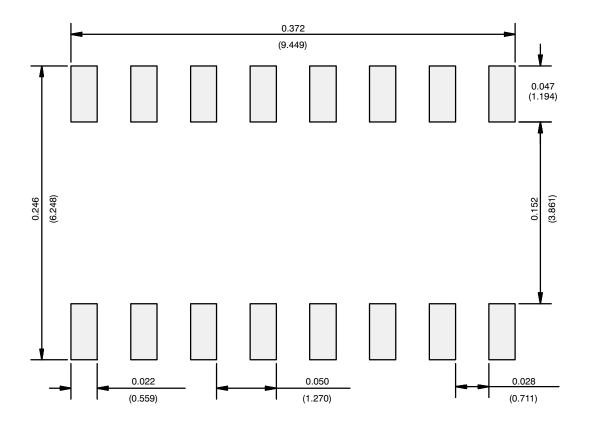
28 Variation HHD is shown for illustration only.

9. Coplanarity applies to the exposed heat sink slug as well as the terminals.

www.vishay.com Document Number: 71921 19-Aug-02



## **RECOMMENDED MINIMUM PADS FOR SO-16**



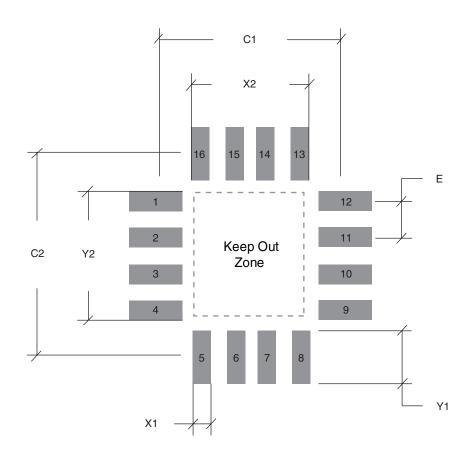
Recommended Minimum Pads Dimensions in Inches/(mm)

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## RECOMMENDED MINIMUM PADS FOR QFN-16 (4 x 4 MM BODY)



	Inches	Millimeters
C1	0.142	3.60
C2	0.142	3.60
E	0.026	0.65
X1	0.014	0.35
X2	0.089	2.25
Y1	0.037	0.95
Y2	0.089	2.25

### Note:

QFN-16 (4 x 4) has an exposed center pad that must not come into contact with any metalized structure on the PCB. This area is considered a Keep Out Zone.





Vishay

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